

P-Channel Power MOSFET

-60V, -14.5A, 68 mΩ

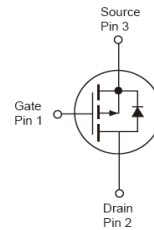
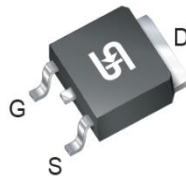
FEATURES

- Improved dV/dt capability
- Fast switching
- Reliability meets AEC-Q101 requirements
- 100% Eas Guaranteed
- Pb-free plating
- RoHS compliant
- Halogen-Free

APPLICATIONS

- Motor Drive
- Power Tools
- LED Lighting

PRODUCT SUMMARY			
PARAMETER		VALUE	UNIT
V_{DS}		-60	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	68	mΩ
	$V_{GS} = -4.5V$	110	
Q_g	$V_{GS} = -10V$	18	nC


TO-252 (DPAK)

Notes: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-60	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current (Note 1)	$T_C = 25^\circ\text{C}$	I_D	-14.5	A
	$T_C = 100^\circ\text{C}$		-9.2	
Pulsed Drain Current (Note 2)		I_{DM}	-58	A
Single Pulse Avalanche Current (Note 3)		I_{AS}	-19.1	A
Single Pulse Avalanche Energy (Note 3)		E_{AS}	18.2	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	20.5	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

THERMAL RESISTANCE			
PARAMETER	SYMBOL	MAXIMUM	UNIT
Thermal Resistance – Junction to Case	$R_{\theta JC}$	6.1	$^\circ\text{C/W}$
Thermal Resistance – Junction to Ambient	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Notes: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design. $R_{\theta JA}$ shown below for single device operation on FR-4 PCB in still air.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-60	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu A$	$V_{GS(TH)}$	-1.2	-1.4	-2.2	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = -60V$	I_{DSS}	--	--	-1	μA
	$V_{GS} = 0V, V_{DS} = -48V$		--	--	-10	
	$T_J = 125^{\circ}C$					
Drain-Source On-State Resistance (Note 3)	$V_{GS} = -10V, I_D = -6A$	$R_{DS(on)}$	--	53.2	68	m Ω
	$V_{GS} = -4.5V, I_D = -3A$		--	67.4	110	
Forward Transconductance	$V_{DS} = -10V, I_D = -6A$	g_{fs}	--	15.3	--	S
Dynamic (Note 5)						
Total Gate Charge	$V_{GS} = -10V, V_{DS} = -30V, I_D = -6A$	Q_g	--	18	--	nC
Gate-Source Charge		Q_{gs}	--	2.8	--	
Gate-Drain Charge		Q_{gd}	--	3.2	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = -30V, f = 1.0MHz$	C_{iss}	--	929	--	pF
Output Capacitance		C_{oss}	--	68	--	
Reverse Transfer Capacitance		C_{rss}	--	55	--	
Gate Resistance	$f = 1.0MHz$	R_g	--	14	--	Ω
Switching (Note 6)						
Turn-On Delay Time	$V_{GS} = -10V, V_{DS} = -30V, I_D = -1A, R_G = 6\Omega$	$t_{d(on)}$	--	6.7	--	nS
Rise Time		t_r	--	8.5	--	
Turn-Off Delay Time		$t_{d(off)}$	--	53	--	
Fall Time		t_f	--	35	--	
Source-Drain Diode						
Diode Forward Voltage (Note 4)	$V_{GS} = 0V, I_S = -1A$	V_{SD}	--	--	-1	V
Reverse Recovery Time	$I_S = -1A,$	t_{rr}	--	11.9	--	nS
Reverse Recovery Charge	$di/dt = 100A/\mu s$	Q_{rr}	--	6.2	--	nC

Notes:

- Current limited by package
- Pulse width limited by the maximum junction temperature
- $L = 0.1\text{mH}$, $V_{GS} = -10V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
- Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.

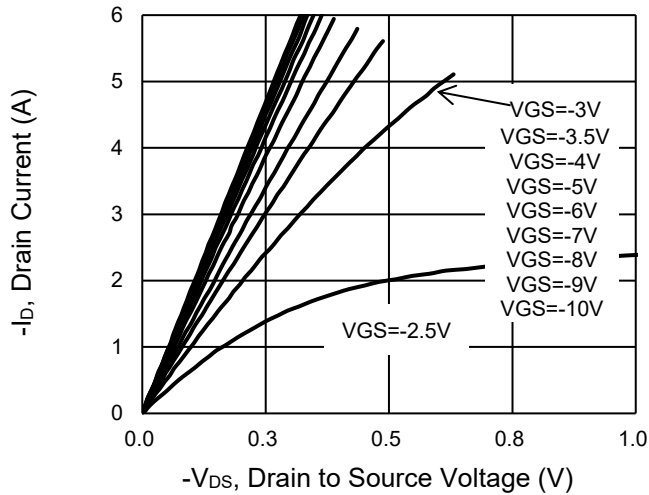
ORDERING INFORMATION

ORDERING CODE	PACKAGE	PACKING
TSM680P06CP ROG	TO-252 (DPAK)	2,500pcs / 13" Reel

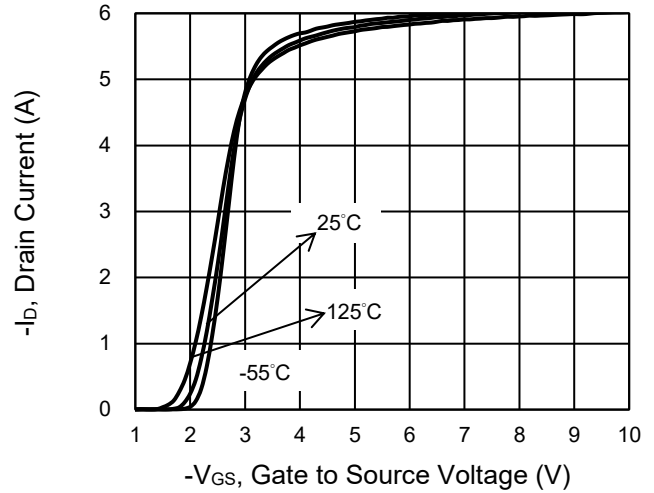
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

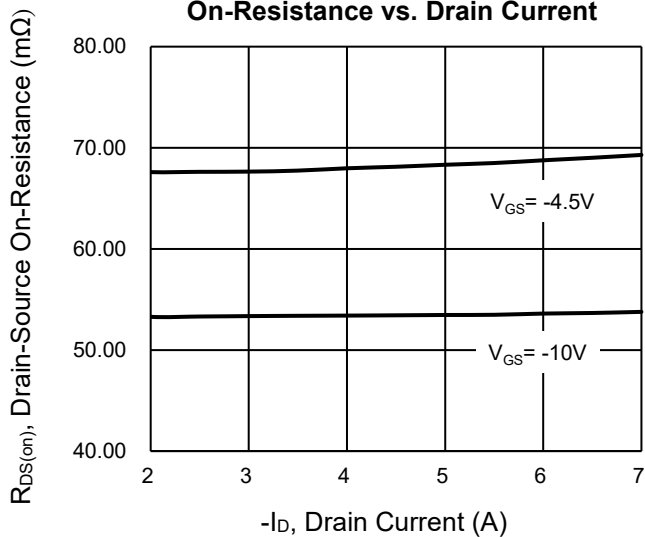
Output Characteristics



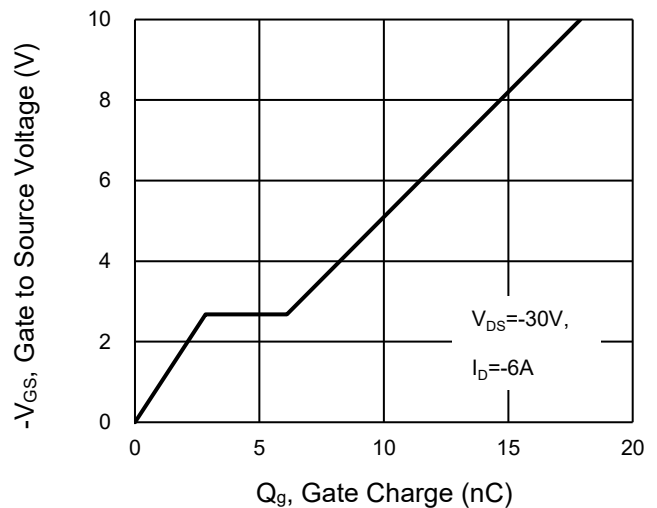
Transfer Characteristics



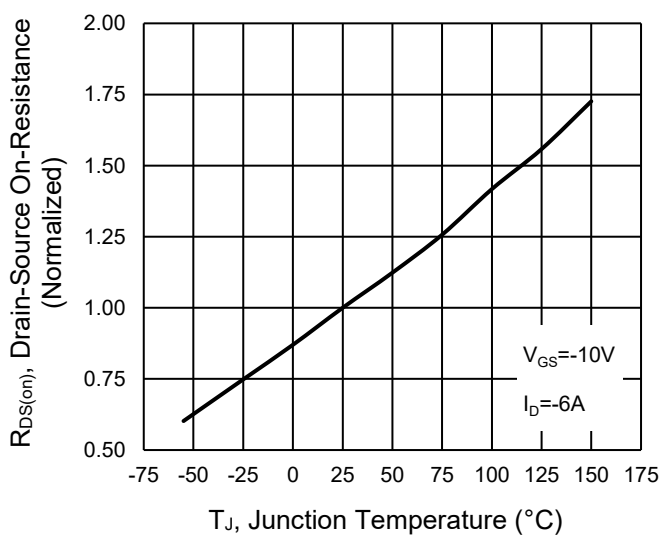
On-Resistance vs. Drain Current



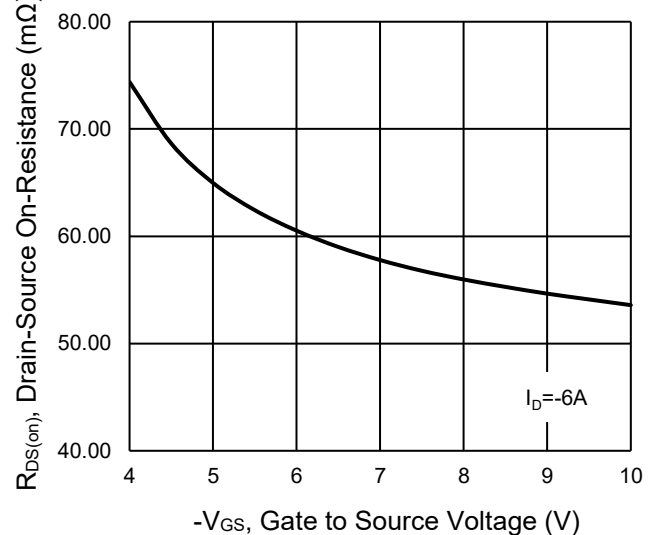
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



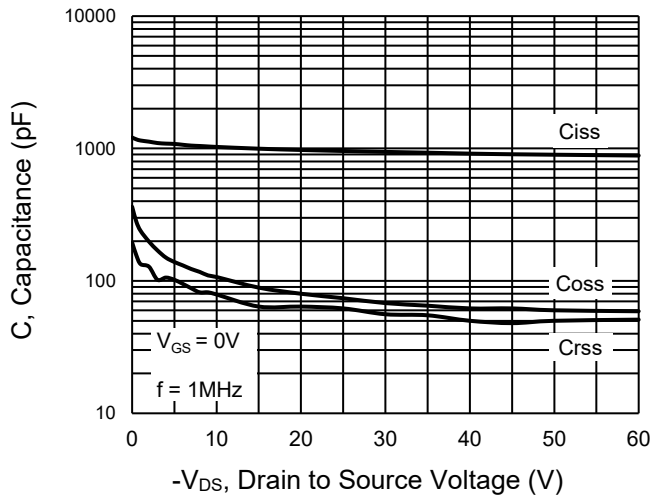
On-Resistance vs. Gate-Source Voltage



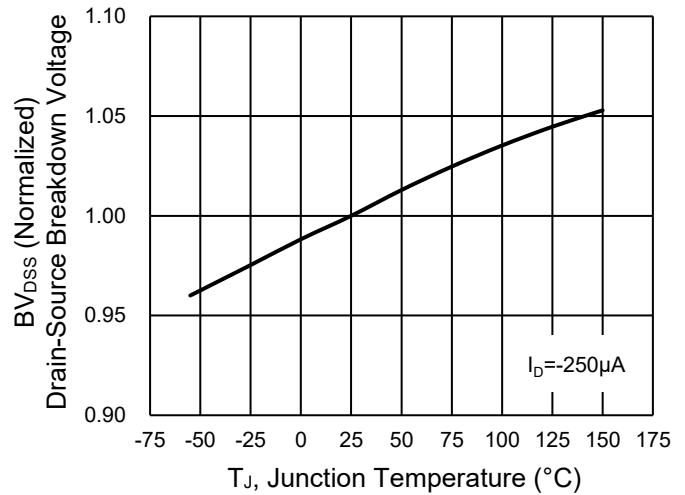
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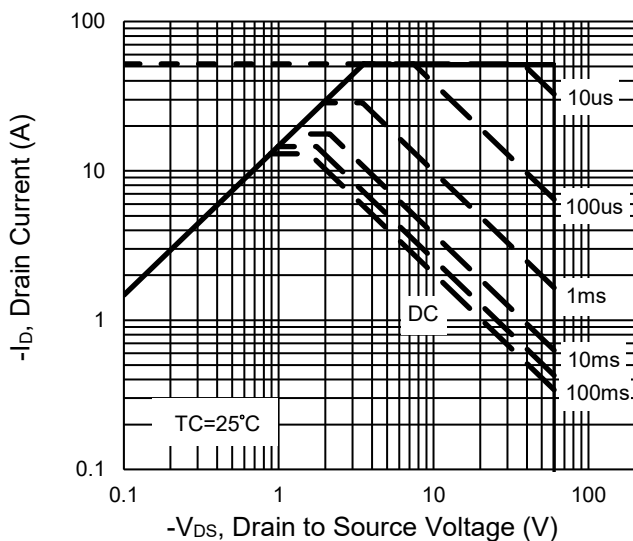
Capacitance vs. Drain-Source Voltage



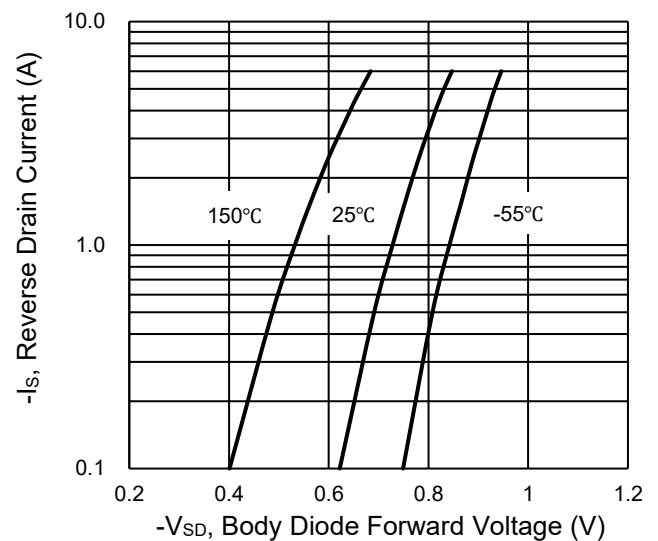
BV_{DSS} vs. Junction Temperature



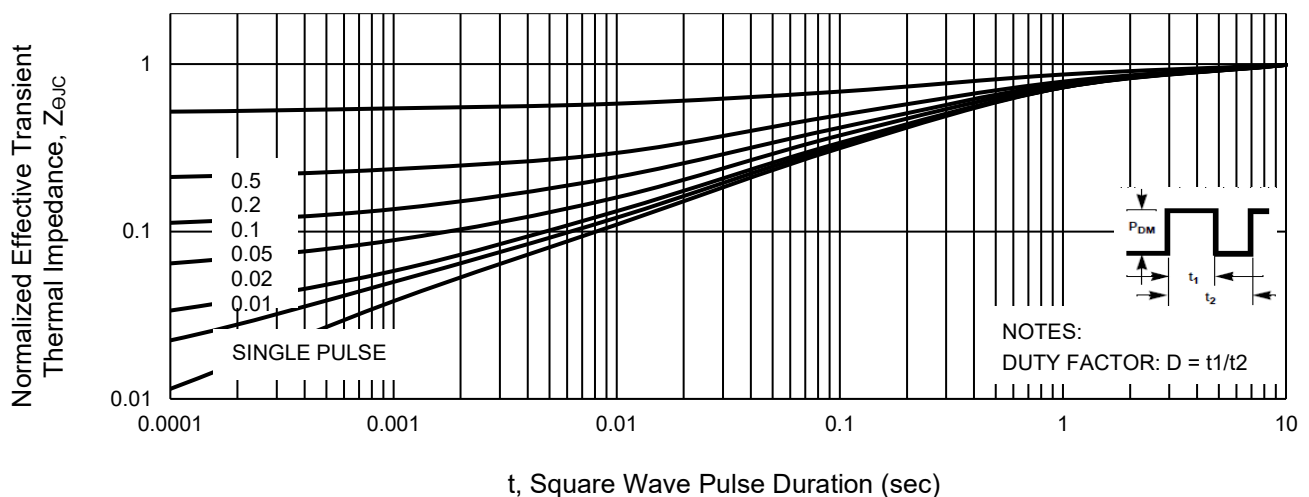
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

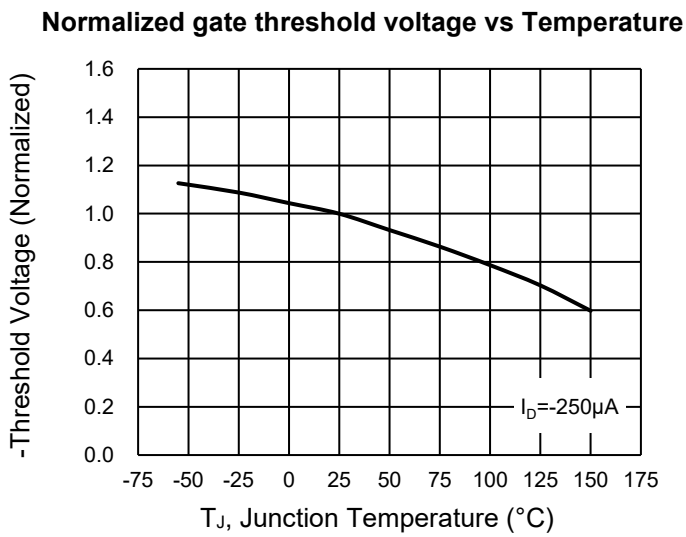
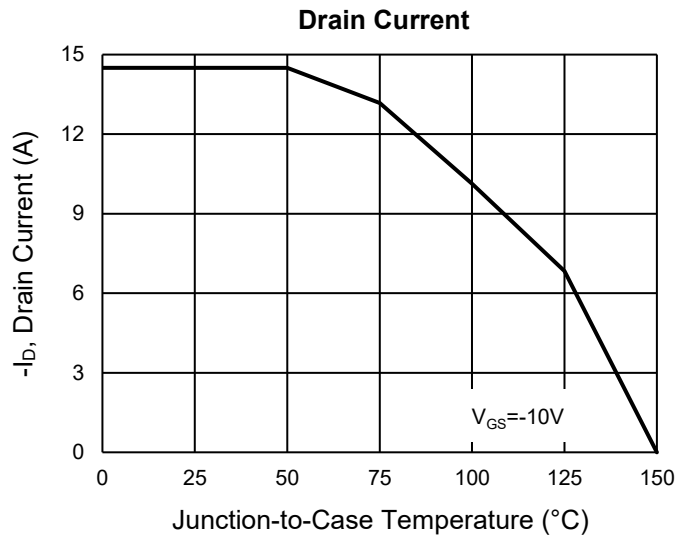
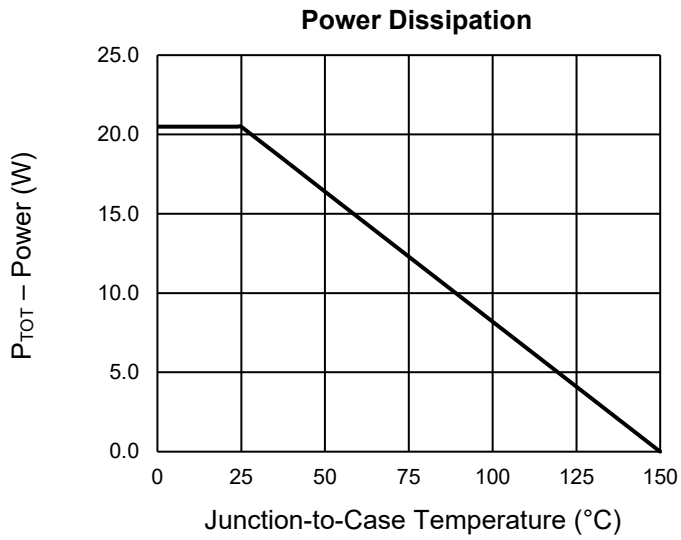


Normalized Thermal Transient Impedance, Junction-to-Case



CHARACTERISTICS CURVES

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